Abstracts

A 60 GHz GaAs FET Amplifier

E.T. Watkins, J.M. Schellenberg, L.H. Hackett, H. Yamasaki and M. Feng. "A 60 GHz GaAs FET Amplifier." 1983 MTT-S International Microwave Symposium Digest 83.1 (1983 [MWSYM]): 145-147.

Using a 1/4 µm gate structure, a new millimeter wave FET device has been developed. This device, in a waveguide/MIC amplifier circuit, has demonstrated gains of 5.0 ±0.5 dB from 55 to 62 GHz with a minimum noise figure of 7.1 dB at 60 GHz.

❏ Return to main document.

Click on title for a complete paper.